

ABSTRACT

Embodiments of the present application disclose an epitaxial deposition method and an epitaxial wafer, and the epitaxial deposition method includes: performing a minority carrier lifetime test on a first epitaxial wafer to obtain minority carrier lifetime of the first epitaxial wafer; determining a first gas flow rate of slit carrier gas introduced into a reactor chamber in a case that the minority carrier lifetime of the first epitaxial wafer is less than a predetermined first threshold; and manufacturing a second epitaxial wafer based on the slit carrier gas of the first gas flow rate.

(Figure 2)